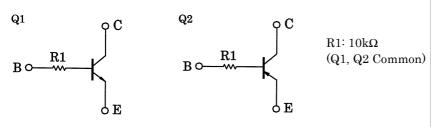
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process) Silicon PNP Epitaxial Type (PCT Process)

RN4991

Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

- Includeing two devices in US6 (ultra super mini type with 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

Equivalent Circuit and Bias Resister Values



Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	IC	100	mA

Unit: mm 2.1 ± 0.1 1.25 ± 0.1 0~0.1 1. EMITTER 1 (E1) (B1) BASE 1 **COLLECTOR 2** (C2) **EMITTER 2** (E2) BASE 2 (B2) US₆ **COLLECTOR 1** (C1) **JEDEC** EIAJ **TOSHIBA** 2-2J1A

Weight: 6.8mg

Q2 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	٧
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I _C	-100	mA

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Q1, Q2 Common Maximum Ratings (Ta = 25°C)

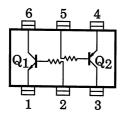
Characteristic	Symbol	Rating	Unit
Collector power dissipation	P _C *	200	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55~150	°C

^{* :} Total rating

Marking



Equivalent Circuit (Top View)



Q1 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	V _{CB} = 50V, I _E = 0	_	_	100	nA
Emitter cut-off current	I _{EBO}	_	V _{EB} = 5V, I _C = 0	_	_	100	mA
DC current gain	h _{FE}	_	V _{CE} = 5V, I _C = 1mA	120	_	700	_
Collector-emitter saturation voltage	V _{CE (sat)}	_	I _C = 5mA, I _B = 0.25mA	_	0.1	0.3	V
Transition frequency	f _T	_	V _{CE} = 10V, I _C = 5mA	_	250	_	MHz
Collector output capacitance	C _{ob}	_	V _{CB} = 10V, I _E = 0, f = 1 MHz	_	3	6	pF

Q2 Electrical Characteristics (Ta = 25°C)

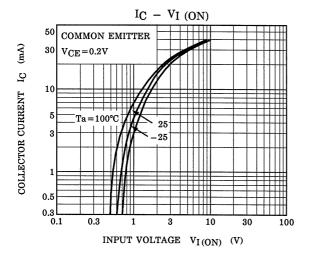
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	V _{CB} = -50V, I _E = 0	_	_	-100	nA
Emitter cut-off current	I _{EBO}	_	$V_{EB} = -5V$, $I_C = 0$	_	_	-100	mA
DC current gain	h _{FE}	_	$V_{CE} = -5V, I_{C} = -1mA$	120	_	400	_
Collector-emitter saturation voltage	V _{CE (sat)}	_	$I_C = -5mA$, $I_B = -0.25mA$	_	-0.1	-0.3	V
Transition frequency	f _T	_	$V_{CE} = -10V, I_{C} = -5mA$	_	200	_	MHz
Collector output capacitance	C _{ob}	_	$V_{CB} = -10V$, $I_E = 0$, $f = 1MHz$	_	3	6	pF

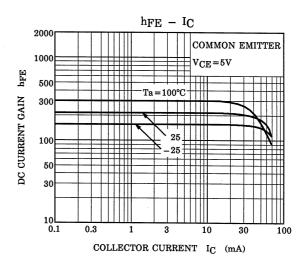
Q1, Q2 Common Electrical Characteristics (Ta = 25°C)

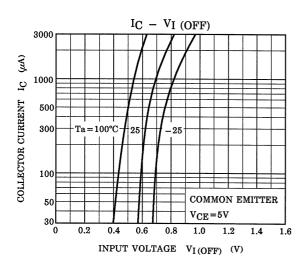
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Input resistor	R1	_	_	7	10	13	kΩ

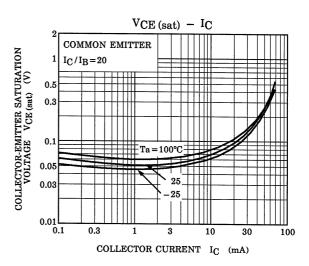
3

Q1

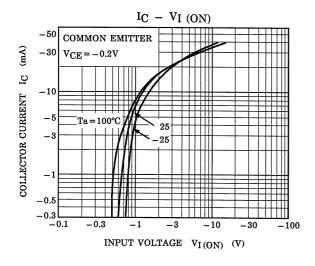


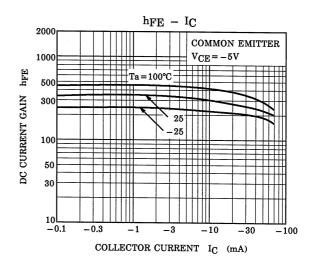


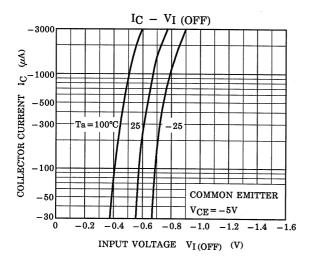


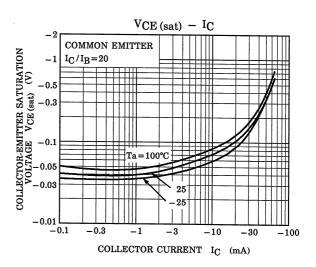


Q2









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